

6/8inch SiC Etcher

Model: SA-GDE C200L

SA-GDE C200L is an upgraded high-density etcher for 6/8-inch wide-bandgap semiconductors including SiC, GaAs and InP. It supports dual clamping modes of ESC and mechanical clamp with wide temperature range from -20°C to 300°C. Equipped with dual-frequency RF and multi-point gas injection, it features flexible process windows and reliable etching performance for diversified compound semiconductor mass production.



Feature

- Symmetric Chamber Design
- High Conductance Pumping System
- Better U%
- PA Control
- Convenient

Application

- BAW
- SiC Power
- VCSEL
- MEMS
- GaN/GaAs RF

Specifications:

Parameter	Descriptions
Wafer Size	6/8inch
Etching Materials	SiC/SiO ₂ /SiN/Polymer/AlScN
Processes	SiC trench/SiC Via/Sic Mark
SRF Frequency	2MHz
SRF Power	2500W
SRF Coil	ICP Cubic
BRF Frequency	13.56MHz
BRF Power	1500W
Wall	RT~80°C(Adjustable)
Upper Electrode	RT°C~120°C(Adjustable)
Bottom Electrode	Clamp chuck:-20~300°C(Max400°C) E chuck:-20~90°C
Wafer Clampage	ESC/Mechanical damp
Turbo Pump	BOC,2650L/s
Injection	TOP,Center
MFC	8 gas/12 gas
EPD	OES/LEP&CCD
Surface Treatment	Roughness coating
Open Method	Electrical

Principle:

